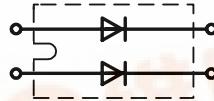




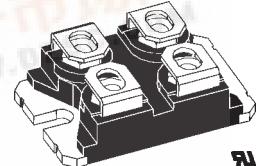
Power Schottky Rectifier

$I_{FAV} = 2 \times 100 \text{ A}$
 $V_{RRM} = 200 \text{ V}$
 $V_F = 0.84 \text{ V}$

V_{RSM}	V_{RRM}	Type
V	V	
200	200	DSS 2x101-02A



miniBLOC,
SOT-227 B



Symbol	Conditions	Maximum Ratings		Features
I_{FRMS}		150	A	
I_{FAVM}	$T_C = 105^\circ\text{C}$; rectangular, $d = 0.5$	100	A	• International standard package miniBLOC
I_{FAVM}	$T_C = 105^\circ\text{C}$; rectangular, $d = 0.5$; per device	200	A	• Isolation voltage 2500 V~
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	1400	A	• UL registered E 72873
E_{AS}	$I_{AS} = 4 \text{ A}$; $L = 100 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	0.8	mJ	• 2 independent Schottky diodes in 1 package
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f = 10 \text{ kHz}$; repetitive	0.4	A	• Very low V_F
$(dv/dt)_{cr}$		18	kV/μs	• Extremely low switching losses
T_{VJ}		-40...+150	°C	• Low I_{RM} -values
T_{VJM}		150	°C	
T_{stg}		-40...+150	°C	
P_{tot}	$T_C = 25^\circ\text{C}$	310	W	
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	2500	V~	
M_d	mounting torque (M4) terminal connection torque (M4)	1.1-1.5/9-13	Nm/lb.in.	
M_d		1.1-1.5/9-13	Nm/lb.in.	
Weight	typical	30	g	

Symbol	Conditions	Characteristic Values		Advantages
		typ.	max.	
I_R	① $V_R = V_{RRM}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	4	mA	• High reliability circuit operation
		10	mA	• Low voltage peaks for reduced protection circuits
V_F	$I_F = 100 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 100 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 200 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.84	V	• Low noise switching
		0.94	V	• Low losses
R_{thJC}	per diode	0.4	K/W	
R_{thCH}	per diode	0.1	K/W	

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0%

Data according to IEC 60747 and per diode unless otherwise specified.

Dimensions see Outlines.pdf

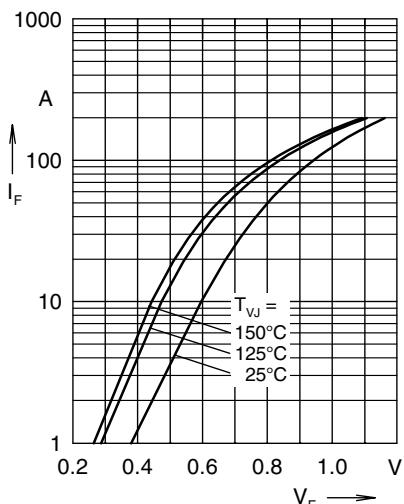


Fig. 1 Max. forward voltage drop characteristics

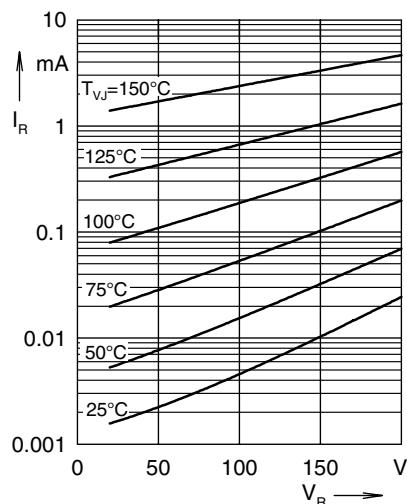


Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

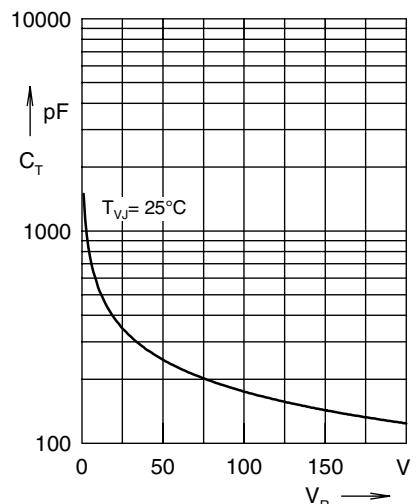


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

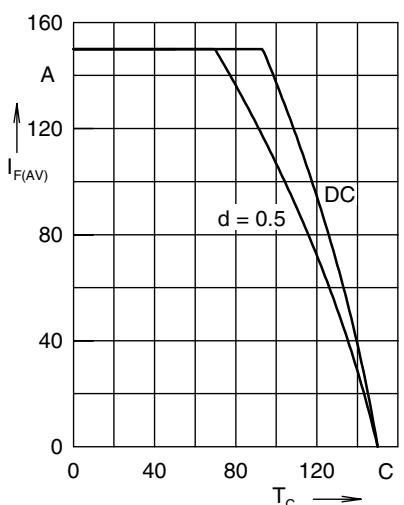


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

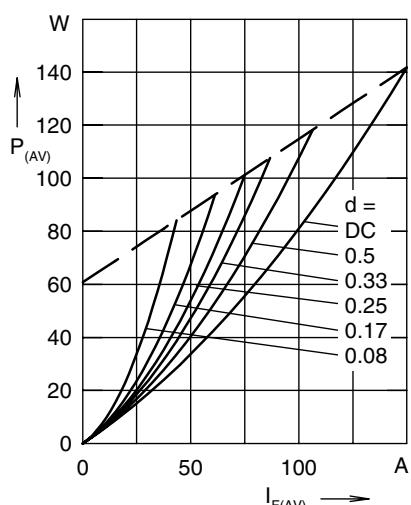


Fig. 5 Forward power loss characteristics

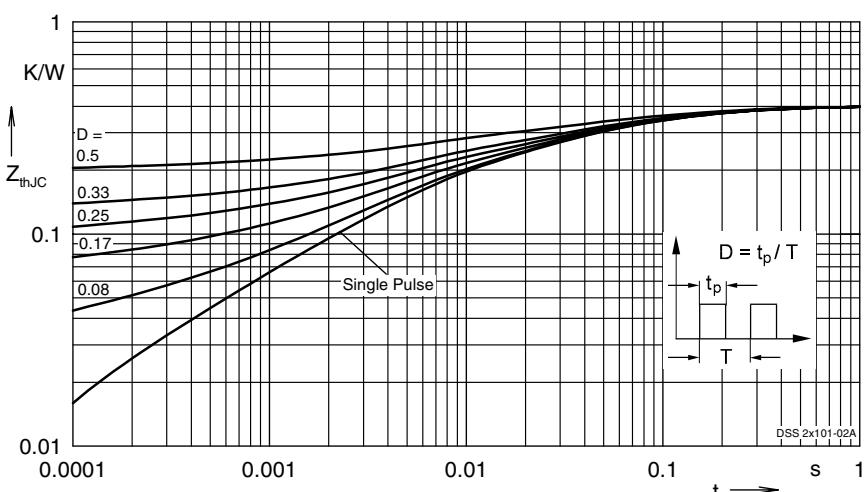


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode